

Title (en)

ORGANIC THIN FILM TRANSISTOR AND METHOD FOR PRODUCING SAME

Title (de)

ORGANISCHER DÜNNSCHICHT-TRANSISTOR UND VERFAHREN ZUR HERSTELLUNG DESSELBEN

Title (fr)

TRANSISTOR À COUCHE MINCE ORGANIQUE ET PROCÉDÉ DE FABRICATION DE CELUI-CI

Publication

EP 3915156 A1 20211201 (DE)

Application

EP 20701710 A 20200117

Priority

- DE 102019200810 A 20190123
- EP 2020051185 W 20200117

Abstract (en)

[origin: CA3127002A1] The invention relates to an organic thin film transistor (OTFT), particularly a thin film field effect transistor (OFET), having a source electrode, a drain electrode, a gate electrode arranged in top gate arrangement, and an organic semiconductor functional layer, wherein the source electrode, the drain electrode and the gate electrode are arranged in a co-planar layer structure, wherein the organic thin film transistor has an intermediate layer for capacitive decoupling of the gate electrode from the source electrode and/or from the source electrode.

IPC 8 full level

H01L 51/00 (2006.01); **H01L 51/05** (2006.01); **H01L 51/10** (2006.01)

CPC (source: EP KR US)

H10K 10/481 (2023.02 - US); **H10K 10/482** (2023.02 - KR); **H10K 10/84** (2023.02 - EP KR US); **H10K 10/88** (2023.02 - US); **H10K 71/233** (2023.02 - KR); **H10K 71/60** (2023.02 - EP KR); **H10K 10/464** (2023.02 - US); **H10K 10/482** (2023.02 - EP); **H10K 71/233** (2023.02 - EP)

Designated contracting state (EPC)

AL AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HR HU IE IS IT LI LT LU LV MC MK MT NL NO PL PT RO RS SE SI SK SM TR

Designated extension state (EPC)

BA ME

DOCDB simple family (publication)

DE 102019200810 A1 20200723; **DE 102019200810 B4 20231207**; CA 3127002 A1 20200730; EP 3915156 A1 20211201; JP 2022516272 A 20220225; KR 20210105973 A 20210827; US 2021391549 A1 20211216; WO 2020152061 A1 20200730; WO 2020152061 A9 20201112

DOCDB simple family (application)

DE 102019200810 A 20190123; CA 3127002 A 20200117; EP 2020051185 W 20200117; EP 20701710 A 20200117; JP 2021538473 A 20200117; KR 20217023292 A 20200117; US 202017418303 A 20200117